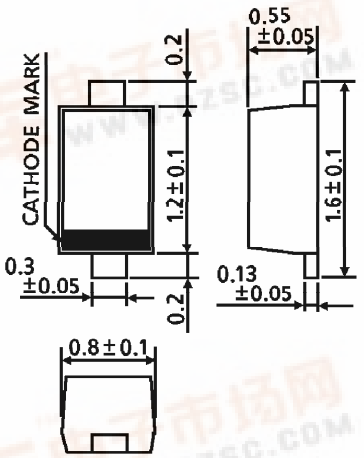
TOSHIBA DIODE SILICON EPITAXIAL PIN TYPE

JDP2S02T

UHF~VHF BAND RF ATTENUATOR APPLICATIONS

Unit in mm

- Suitable for reducing set's size as a result from enabling high-density mounting due to 2-pin small packages.
- Low Series Resistance : r_s = 1.0 Ω (Typ.)
- Low Capacitance : C_T = 0.3 pF (Typ.)



TESC	
JEDEC	—
EIAJ	—
TOSHIBA	1-1H1A

Weight : 0.0013 g

MAXIMUM RATINGS (Ta = 25°C)

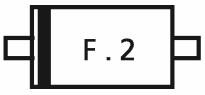
CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	30	V
Foward Current	I_F	50	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	I_R = 10 μA	30	—	—	V
Reverse Current	I_R	V_R = 30 V	—	—	0.1	μA
Forward Voltage	V_F	I_F = 50 mA	—	0.9	0.95	V
Capacitance	C_T	V_R = 1 V, f = 1 MHz	—	0.3	0.5	pF
Series Resistance	r_s	I_F = 10 mA, f = 100 MHz	—	1.0	1.5	Ω

* Signal level when capacitance is measured : Vsig = 20 mV_{rms}

MARKING



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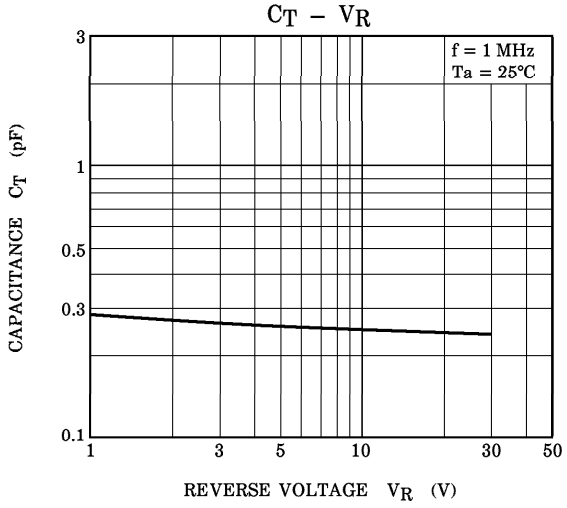
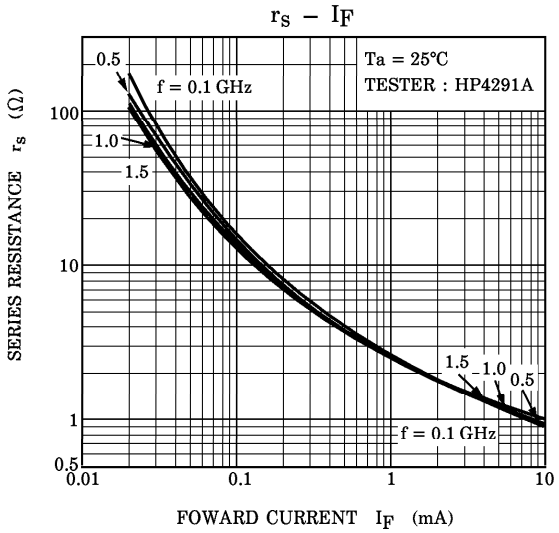

$C_T - V_R$
f = 1 MHz
Ta = 25°C
CAPACITANCE C_T (pF)
3
1
0.5
0.3
0.1
1
3
5
10
30
50
REVERSE VOLTAGE V_R (V)


$r_S - I_F$
Ta = 25°C
TESTER : HP4291A
f = 0.1 GHz
0.5
1.0
1.5
SERIES RESISTANCE r_S (Ω)
100
10
1
0.5
0.01
0.1
1
10
FOWARD CURRENT I_F (mA)